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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M0
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	CANbus, HDMI-CEC, I ² C, IrDA, LINbus, SPI, UART/USART, USB
Peripherals	DMA, I ² S, POR, PWM, WDT
Number of I/O	23
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	6K x 8
Voltage - Supply (Vcc/Vdd)	1.65V ~ 1.95V
Data Converters	A/D 10x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	28-UFQFN
Supplier Device Package	28-UFQFPN (4x4)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f048g6u6

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

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Perip	heral	STM32F048G6	STM32F048T6	STM32F048C6		
Flash mem	ory (Kbyte)		32			
SRAM (Kbyte)		6				
Timoro	Advanced control		1 (16-bit)			
Timers	General purpose	4 (16-bit) 1 (32-bit)				
	SPI [I2S] ⁽¹⁾	1 [1] 2 [1]				
	l ² C	1				
Comm. interfaces	USART	2				
	USB	1				
	CEC	1				
	t ADC f channels)	1 (10 ext. + 3 int.)				
GP	IOs	23	29	37		
Capacitive ser	nsing channels	10	13	13		
Max. CPU	frequency	48 MHz				
Operatin	g voltage	V_{DD} = 1.8 V ± 8%, V_{DDA} = from V_{DD} to 3.6 V				
Operating t	emperature	Ambient operating temperature: -40°C to 85 °C / -40°C to 105°C Junction temperature: -40°C to 105°C / -40°C to 125°C				
Pack	ages	UFQFPN28	WLCSP36	UFQFPN48		

Table 1. STM32F048x device features and peripheral counts

1. The SPI1 interface can be used either in SPI mode or in I2S audio mode.



3 Functional overview

Figure 1 shows the general block diagram of the STM32F048x6 devices.

3.1 ARM[®]-Cortex[®]-M0 core

The ARM[®] Cortex[®]-M0 is a generation of ARM 32-bit RISC processors for embedded systems. It has been developed to provide a low-cost platform that meets the needs of MCU implementation, with a reduced pin count and low-power consumption, while delivering outstanding computational performance and an advanced system response to interrupts.

The ARM[®] Cortex[®]-M0 processors feature exceptional code-efficiency, delivering the high performance expected from an ARM core, with memory sizes usually associated with 8- and 16-bit devices.

The STM32F048x6 devices embed ARM core and are compatible with all ARM tools and software.

3.2 Memories

The device has the following features:

- 6 Kbytes of embedded SRAM accessed (read/write) at CPU clock speed with 0 wait states and featuring embedded parity checking with exception generation for fail-critical applications.
- The non-volatile memory is divided into two arrays:
 - 32 Kbytes of embedded Flash memory for programs and data
 - Option bytes

The option bytes are used to write-protect the memory (with 4 KB granularity) and/or readout-protect the whole memory with the following options:

- Level 0: no readout protection
- Level 1: memory readout protection, the Flash memory cannot be read from or written to if either debug features are connected or boot in RAM is selected
- Level 2: chip readout protection, debug features (Cortex[®]-M0 serial wire) and boot in RAM selection disabled

3.3 Boot modes

At startup, the boot pin and boot selector option bits are used to select one of the three boot options:

- boot from User Flash memory
- boot from System Memory
- boot from embedded SRAM

The boot pin is shared with the standard GPIO and can be disabled through the boot selector option bits. The boot loader is located in System Memory. It is used to reprogram the Flash memory by using USART on pins PA14/PA15 or PA9/PA10 or I²C on pins PB6/PB7 or through the USB DFU interface.

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3.4 Cyclic redundancy check calculation unit (CRC)

The CRC (cyclic redundancy check) calculation unit is used to get a CRC code from a 32-bit data word and a CRC-32 (Ethernet) polynomial.

Among other applications, CRC-based techniques are used to verify data transmission or storage integrity. In the scope of the EN/IEC 60335-1 standard, they offer a means of verifying the Flash memory integrity. The CRC calculation unit helps compute a signature of the software during runtime, to be compared with a reference signature generated at link-time and stored at a given memory location.

3.5 **Power management**

3.5.1 Power supply schemes

- $V_{DD} = V_{DDIO1} = 1.8 \text{ V} \pm 8\%$: external power supply for I/Os (V_{DDIO1}) and digital logic. It is provided externally through VDD pins.
- V_{DDA} = from V_{DD} to 3.6 V: external analog power supply for ADC, RCs and PLL (minimum voltage to be applied to V_{DDA} is 2.4 V when the ADC is used). It is provided externally through VDDA pin. The V_{DDA} voltage level must be always greater or equal to the V_{DD} voltage level and must be established first.
- V_{DDIO2} = 1.65 to 3.6 V: external power supply for marked I/Os. V_{DDIO2} is provided externally through the VDDIO2 pin. The V_{DDIO2} voltage level is completely independent from V_{DD} or V_{DDA}, but it must not be provided without a valid supply on V_{DD}. The V_{DDIO2} supply is monitored and compared with the internal reference voltage (V_{REFINT}). When the V_{DDIO2} is below this threshold, all the I/Os supplied from this rail are disabled by hardware. The output of this comparator is connected to EXTI line 31 and it can be used to generate an interrupt. Refer to the pinout diagrams or tables for concerned I/Os list.
- V_{BAT} = 1.65 to 3.6 V: power supply for RTC, external clock 32 kHz oscillator and backup registers (through power switch) when V_{DD} is not present.

For more details on how to connect power pins, refer to *Figure 9: Power supply scheme*.

3.5.2 Power-on reset

To guarantee a proper power-on reset, the NPOR pin must be held low until V_{DD} is stable. When V_{DD} is stable, the reset state can be exited either by:

- putting the NPOR pin in high impedance (NPOR pin has an internal pull-up), or by
- forcing the pin to high level by connecting it to V_{DDA}

3.5.3 Low-power modes

The STM32F048x6 microcontrollers support two low-power modes to achieve the best compromise between low power consumption, short startup time and available wakeup sources:

Sleep mode

In Sleep mode, only the CPU is stopped. All peripherals continue to operate and can wake up the CPU when an interrupt/event occurs.



TIM16 and TIM17 have a complementary output with dead-time generation and independent DMA request generation.

Their counters can be frozen in debug mode.

3.12.3 Independent watchdog (IWDG)

The independent watchdog is based on an 8-bit prescaler and 12-bit downcounter with user-defined refresh window. It is clocked from an independent 40 kHz internal RC and as it operates independently from the main clock, it can operate in Stop mode. It can be used either as a watchdog to reset the device when a problem occurs, or as a free running timer for application timeout management. It is hardware or software configurable through the option bytes. The counter can be frozen in debug mode.

3.12.4 System window watchdog (WWDG)

The system window watchdog is based on a 7-bit downcounter that can be set as free running. It can be used as a watchdog to reset the device when a problem occurs. It is clocked from the APB clock (PCLK). It has an early warning interrupt capability and the counter can be frozen in debug mode.

3.12.5 SysTick timer

This timer is dedicated to real-time operating systems, but could also be used as a standard down counter. It features:

- a 24-bit down counter
- autoreload capability
- maskable system interrupt generation when the counter reaches 0
- programmable clock source (HCLK or HCLK/8)

3.13 Real-time clock (RTC) and backup registers

The RTC and the five backup registers are supplied through a switch that takes power either on V_{DD} supply when present or through the V_{BAT} pin. The backup registers are five 32-bit registers used to store 20 bytes of user application data when V_{DD} power is not present. They are not reset by a system or power reset.



from the CPU clock, allowing the I2C1 to wake up the MCU from Stop mode on address match.

The I2C peripheral can be served by the DMA controller.

Table 8. STM32F048x6 I ² C implementation				
I ² C features ⁽¹⁾	I2C1			
7-bit addressing mode	Х			
10-bit addressing mode	Х			
Standard mode (up to 100 kbit/s)	Х			
Fast mode (up to 400 kbit/s)	Х			
Fast Mode Plus with extra output drive I/Os (up to 1 Mbit/s)	Х			
Independent clock	Х			
SMBus	Х			
Wakeup from STOP	X			

1. X = supported.

3.15 Universal synchronous/asynchronous receiver/transmitter (USART)

The device embeds two universal synchronous/asynchronous receivers/transmitters (USART1, USART2) which communicate at speeds of up to 6 Mbit/s.

They provide hardware management of the CTS, RTS and RS485 DE signals, multiprocessor communication mode, master synchronous communication and single-wire half-duplex communication mode. USART1 supports also SmartCard communication (ISO 7816), IrDA SIR ENDEC, LIN Master/Slave capability and auto baud rate feature, and has a clock domain independent of the CPU clock, allowing to wake up the MCU from Stop mode.

The USART interfaces can be served by the DMA controller.

USART modes/features ⁽¹⁾	USART1	USART2				
Hardware flow control for modem	Х	Х				
Continuous communication using DMA	Х	Х				
Multiprocessor communication	Х	Х				
Synchronous mode	Х	Х				
Smartcard mode	Х	-				
Single-wire half-duplex communication	Х	Х				
IrDA SIR ENDEC block	Х	-				
LIN mode	Х	-				
Dual clock domain and wakeup from Stop mode	Х	-				
Receiver timeout interrupt	Х	-				

Table 9. STM32F048x6 USART implementation



pull-up and also battery charging detection according to Battery Charging Specification Revision 1.2. The USB interface implements a full-speed (12 Mbit/s) function interface with added support for USB 2.0 Link Power Management. It has software-configurable endpoint setting with packet memory up-to 1 KB and suspend/resume support. It requires a precise 48 MHz clock which can be generated from the internal main PLL (the clock source must use an HSE crystal oscillator) or by the internal 48 MHz oscillator in automatic trimming mode. The synchronization for this oscillator can be taken from the USB data stream itself (SOF signalization) which allows crystal-less operation.

3.19 Clock recovery system (CRS)

The STM32F048x6 embeds a special block which allows automatic trimming of the internal 48 MHz oscillator to guarantee its optimal accuracy over the whole device operational range. This automatic trimming is based on the external synchronization signal, which could be either derived from USB SOF signalization, from LSE oscillator, from an external signal on CRS_SYNC pin or generated by user software. For faster lock-in during startup it is also possible to combine automatic trimming with manual trimming action.

3.20 Serial wire debug port (SW-DP)

An ARM SW-DP interface is provided to allow a serial wire debugging tool to be connected to the MCU.



4 Pinouts and pin descriptions

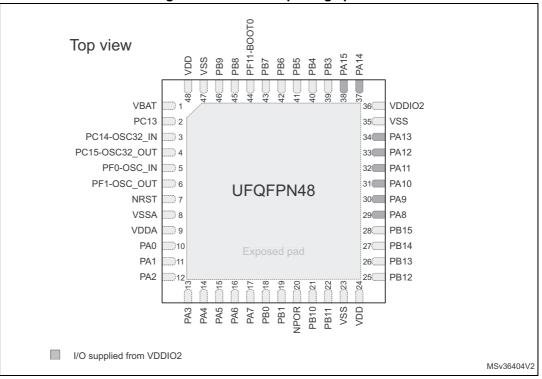
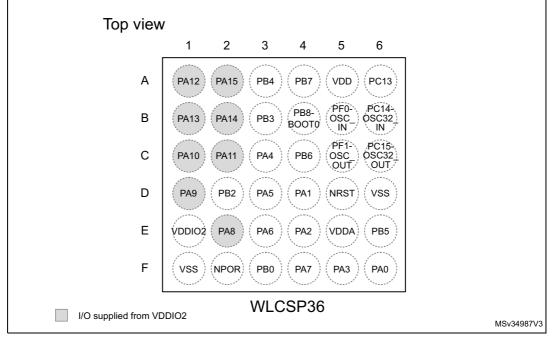


Figure 3. UFQFPN48 package pinout





^{1.} The above figure shows the package in top view, changing from bottom view in the previous document versions.

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Pir	n numt	pers					n definitions Pin functions	5	
UFQFPN48	WLCSP36	UFQFPN28	Pin name (function upon reset)	Pin type	I/O structure	Notes	Alternate function	Additional functions	
1	-	-	VBAT	S	-	-	Backup power su	pply	
2	A6	-	PC13	I/O	тс	(1)(2)	-	WKUP2, RTC_TAMP1, RTC_TS, RTC_OUT	
3	B6	-	PC14-OSC32_IN (PC14)	I/O	тс	(1) (2)	-	OSC32_IN	
4	C6	-	PC15-OSC32_OUT (PC15)	I/O	тс	(1) (2)	-	OSC32_OUT	
5	B5	2	PF0-OSC_IN (PF0)	I/O	FTf	-	CRS_SYNC I2C1_SDA	OSC_IN	
6	C5	3	PF1-OSC_OUT (PF1)	I/O	FTf	-	I2C1_SCL	OSC_OUT	
7	D5	4	NRST	I/O	RST	-	Device reset input / internal reset output (activ low)		
8	D6	16	VSSA	S		(3)	Analog ground	t	
9	E5	5	VDDA	S		-	Analog power su	pply	
10	F6	6	PA0	I/O	ТТа	-	USART2_CTS, TIM2_CH1_ETR, TSC_G1_IO1	RTC_TAMP2, WKUP1, ADC_IN0,	
11	D4	7	PA1	I/O	ТТа	-	USART2_RTS, TIM2_CH2, TSC_G1_IO2, EVENTOUT	ADC_IN1	
12	E4	8	PA2	I/O	ТТа	-	USART2_TX, TIM2_CH3, TSC_G1_IO3	ADC_IN2, WKUP4	
13	F5	9	PA3	I/O	ТТа	-	USART2_RX, TIM2_CH4, TSC_G1_IO4	ADC_IN3	
14	C3	10	PA4	I/O	ТТа	-	SPI1_NSS, I2S1_WS, TIM14_CH1, TSC_G2_IO1, USART2_CK USB_NOE	ADC_IN4	
15	D3	11	PA5	I/O	ТТа	-	SPI1_SCK, I2S1_CK, CEC, TIM2_CH1_ETR, TSC_G2_IO2	ADC_IN5	
16	E3	12	PA6	I/O	TTa	-	SPI1_MISO, I2S1_MCK, TIM3_CH1, TIM1_BKIN, TIM16_CH1, TSC_G2_IO3, EVENTOUT	ADC_IN6	

Table 12. STM32F048x6 pin definitions



6.3 Operating conditions

6.3.1 General operating conditions

Table 20. Ger	neral operating	conditions	5

Symbol	Parameter	Conditions	Min	Max	Unit	
f _{HCLK}	Internal AHB clock frequency -		0	48	MHz	
f _{PCLK}	Internal APB clock frequency	-	0	48		
V _{DD}	Standard operating voltage	-	1.65	1.95	V	
V _{DDIO2}	I/O supply voltage	Must not be supplied if V_{DD} is not present	1.65	3.6	V	
V	Analog operating voltage (ADC not used)	Must have a potential equal	V _{DD}	3.6	V	
V DDA	Analog operating voltage (ADC used)		2.4	3.6	v	
V _{BAT}	Backup operating voltage	-	1.65	3.6	V	
		TC and RST I/O	-0.3	V _{DDIOx} +0.3		
V _{IN}	I/O input voltage	TTa and POR I/O	-0.3	V _{DDA} +0.3 ⁽¹⁾	V	
		FT and FTf I/O		5.2 ⁽¹⁾		
	Power dissipation at $T_A = 85 \degree C$	UFQFPN48	-	606		
P _D	for suffix 6 or $T_{\Delta} = 105$ °C for	WLCSP36	-	313	mW	
	suffix 7 ⁽²⁾	UFQFPN28	-	170		
	Ambient temperature for the	Maximum power dissipation	-40	85	°C	
Та	suffix 6 version	Low power dissipation ⁽³⁾	-40	105	C	
IA	Ambient temperature for the	Maximum power dissipation	-40	105	З°	
	suffix 7 version	Low power dissipation ⁽³⁾	-40	125	U	
TJ	lunction temporature range	Suffix 6 version	-40	105	°C	
IJ	Junction temperature range	Suffix 7 version	-40	125	U	

1. For operation with a voltage higher than V_{DDIOx} + 0.3 V, the internal pull-up resistor must be disabled.

2. If T_A is lower, higher P_D values are allowed as long as T_J does not exceed T_{Jmax} . See Section 7.4: Thermal characteristics.

3. In low power dissipation state, T_A can be extended to this range as long as T_J does not exceed T_{Jmax} (see Section 7.4: *Thermal characteristics*).

6.3.2 Operating conditions at power-up / power-down

The parameters given in *Table 21* are derived from tests performed under the ambient temperature condition summarized in *Table 20*.



	Table 23. Typical and maximum current consumption from V_{DD} supply at $V_{DD} = 1.8 V$ All peripherals enabled ⁽¹⁾ All peripherals disabled											
0	eter			All				All	· ·			-
Symbol	Parameter	Conditions	f _{HCLK}	Tun	N	lax @ T _A	(2)	Tun	M	ax @ T _A	(2)	Unit
ίΩ,	Sy			Тур	25 °C	85 °C	105 °C	Тур	25 °C	85 °C	105 °C	
	,	HSI48	48 MHz	19.0	20.4	20.9	21.3	11.7	12.2	12.8	12.9	
	Supply current in Run mode, code executing from Flash memory		48 MHz	18.5	20.0	20.5	20.9	11.5	12.1	12.6	12.8	
	mod	External	32 MHz	12.5	13.2	13.6	14.0	7.8	8.4	8.7	8.9	
	Run I	clock (HSE	24 MHz	10.1	10.4	10.7	11.0	6.2	6.6	6.9	7.1	
	t in F om F	bypass)	8 MHz	3.5	4.0	4.1	4.2	2.3	2.5	2.6	2.6	mA
	Supply current in Run mode, le executing from Flash mem		1 MHz	0.7	0.8	0.9	1.0	0.5	0.7	0.7	0.8	III.
	y cu cutir		48 MHz	18.7	20.2	20.6	21.0	11.6	12.1	12.7	12.8	
	uppl	Internal	32 MHz	12.7	13.4	13.8	14.2	8.0	8.6	8.8	9.1	
	S	clock (HSI)	24 MHz	10.2	10.6	11.0	11.1	6.3	6.8	7.0	7.1	
	0		8 MHz	3.7	4.2	4.3	4.5	2.3	2.5	2.6	2.7	
		HSI48	48 MHz	18.2	19.6	20.0	20.4	10.9	11.4	12.0	12.2	
	aĵ	Code executive function RAM External clock (HSE bypass)	48 MHz	17.8	19.2	19.7	20.0	10.7	11.4	11.9	12.1	
	node RAM		32 MHz	12.1	12.6	13.0	13.4	7.2	7.6	8.0	8.3	
	un r om F		24 MHz	9.6	9.9	10.1	10.4	5.6	5.9	6.3	6.5	
	in F ng fr		8 MHz	3.0	3.4	3.6	3.7	1.6	2.0	2.0	2.0	
I _{DD}	rrent		1 MHz	0.4	0.5	0.6	0.7	0.2	0.3	0.3	0.4	
	Supply current in Run mode, code executing from RAM		48 MHz	18.0	19.4	19.9	20.2	10.8	11.4	12.0	12.1	
	uppl	Internal	32 MHz	12.3	12.9	13.2	13.6	7.4	7.8	8.2	8.4	
	Ō	clock (HSI)	24 MHz	9.8	10.1	10.4	10.6	5.7	5.9	6.3	6.5	
			8 MHz	3.2	3.6	3.7	3.9	1.7	2.1	2.1	2.2	mA
		HSI48	48 MHz	10.9	12.2	13.0	13.3	2.7	2.8	2.9	3.1	
	e		48 MHz	10.7	12.1	12.8	13.1	2.6	2.7	2.8	3.0	
	bom	External	32 MHz	7.8	8.3	8.6	9.0	1.7	1.9	2.0	2.3	
	leep	clock (HSE	24 MHz	6.2	6.8	7.2	7.4	1.4	1.4	1.6	1.6	
	in S	bypass)	8 MHz	2.0	2.5	2.6	2.7	0.5	0.5	0.6	0.6	
	rent		1 MHz	0.3	0.3	0.4	0.5	0.1	0.2	0.2	0.2	
	, cur		48 MHz	10.8	12.1	12.9	13.2	2.6	2.7	2.8	3.0	
	Supply current in Sleep mode	Internal	32 MHz	7.9	8.4	8.7	9.2	1.9	2.0	2.1	2.3	
	SL	clock (HSI)	24 MHz	6.3	6.9	7.3	7.5	1.4	1.4	1.6	1.7	
			8 MHz	2.0	2.6	2.7	2.8	0.5	0.6	0.6	0.8	

Table 23. Typical and maximum	current consumption from V_{DD} supply at V_{DD} = 1.8 V

1. USB is kept disabled as this IP functions only with a 48 MHz clock.

2. Data based on characterization results, not tested in production unless otherwise specified.



6.3.5 Wakeup time from low-power mode

The wakeup times given in *Table 30* are the latency between the event and the execution of the first user instruction. The device goes in low-power mode after the WFE (Wait For Event) instruction, in the case of a WFI (Wait For Interruption) instruction, 16 CPU cycles must be added to the following timings due to the interrupt latency in the Cortex M0 architecture.

The SYSCLK clock source setting is kept unchanged after wakeup from Sleep mode. During wakeup from Stop mode, SYSCLK takes the default setting: HSI 8 MHz.

The wakeup source from Sleep and Stop mode is an EXTI line configured in event mode.

All timings are derived from tests performed under the ambient temperature and supply voltage conditions summarized in *Table 20: General operating conditions*.

Symbol	Parameter	Тур @	V _{DDA}	Мах	Unit
Symbol	rarameter	= 1.8 V	= 3.3 V	WIAA	Onic
t _{WUSTOP}	Wakeup from Stop mode	3.5	2.8	5.3	μs
t _{WUSLEEP}	Wakeup from Sleep mode	4 SYSCL	K cycles	-	μs

Table 30. Low-power mode wakeup timings

6.3.6 External clock source characteristics

High-speed external user clock generated from an external source

In bypass mode the HSE oscillator is switched off and the input pin is a standard GPIO.

The external clock signal has to respect the I/O characteristics in Section 6.3.13. However, the recommended clock input waveform is shown in *Figure 11: High-speed external clock source AC timing diagram*.

Symbol	Parameter ⁽¹⁾	Min	Тур	Max	Unit
f _{HSE_ext}	User external clock source frequency	-	8	32	MHz
V _{HSEH}	OSC_IN input pin high level voltage	0.7 V _{DDIOx}	-	V _{DDIOx}	V
V _{HSEL}	OSC_IN input pin low level voltage	V _{SS}	-	0.3 V _{DDIOx}	v
t _{w(HSEH)} t _{w(HSEL)}	OSC_IN high or low time	15	-	-	ns
t _{r(HSE)} t _{f(HSE)}	OSC_IN rise or fall time	-	-	20	115

Table 31. High-speed external user clock characteristics

1. Guaranteed by design, not tested in production.



High-speed external clock generated from a crystal/ceramic resonator

The high-speed external (HSE) clock can be supplied with a 4 to 32 MHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on design simulation results obtained with typical external components specified in *Table 33*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Symbol	Parameter	Conditions ⁽¹⁾	Min ⁽²⁾	Тур	Max ⁽²⁾	Unit
f _{OSC_IN}	Oscillator frequency	-	4	8	32	MHz
R _F	Feedback resistor	-	-	200	-	kΩ
		During startup ⁽³⁾	-	-	8.5	
		V _{DD} = 1.8 V, Rm = 30 Ω, CL = 10 pF@8 MHz	-	0.4	-	
	HSE current consumption	V _{DD} = 1.8 V, Rm = 45 Ω, CL = 10 pF@8 MHz	-	0.5	-	
I _{DD}		V _{DD} = 1.8 V, Rm = 30 Ω, CL = 5 pF@32 MHz	-	0.8	-	mA
		V _{DD} = 1.8 V, Rm = 30 Ω, CL = 10 pF@32 MHz	-	1	-	
		V _{DD} = 1.8 V, Rm = 30 Ω, CL = 20 pF@32 MHz	-	1.5	-	
9 _m	Oscillator transconductance	Startup	10	-	-	mA/V
t _{SU(HSE)} ⁽⁴⁾	Startup time	V _{DD} is stabilized	-	2	-	ms

1. Resonator characteristics given by the crystal/ceramic resonator manufacturer.

2. Guaranteed by design, not tested in production.

3. This consumption level occurs during the first 2/3 of the $t_{\mbox{SU(HSE)}}$ startup time

4. t_{SU(HSE)} is the startup time measured from the moment it is enabled (by software) to a stabilized 8 MHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer

For C_{L1} and C_{L2}, it is recommended to use high-quality external ceramic capacitors in the 5 pF to 20 pF range (Typ.), designed for high-frequency applications, and selected to match the requirements of the crystal or resonator (see *Figure 13*). C_{L1} and C_{L2} are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2}. PCB and MCU pin capacitance must be included (10 pF can be used as a rough estimate of the combined pin and board capacitance) when sizing C_{L1} and C_{L2}.

Note: For information on selecting the crystal, refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website www.st.com.



Symbol	Ratings	Conditions	Packages	Class	Maximum value ⁽¹⁾	Unit	
V _{ESD(HBM)}	Electrostatic discharge voltage (human body model)	$T_A = +25 \degree C$, conforming to JESD22-A114	All	2	2000	V	
V _{ESD(CDM)}	Electrostatic discharge voltage (charge device model)	$T_A = +25 \degree C$, conforming to ANSI/ESD STM5.3.1	All	C4	500	V	

Table 44. ESD absolute maximum ratings

1. Data based on characterization results, not tested in production.

Static latch-up

Two complementary static tests are required on six parts to assess the latch-up performance:

- A supply overvoltage is applied to each power supply pin.
- A current injection is applied to each input, output and configurable I/O pin.

These tests are compliant with EIA/JESD 78A IC latch-up standard.

Table 45. Electrical sensitivities

Symbol	Parameter	Conditions	Class
LU	Static latch-up class	$T_A = +105 \text{ °C conforming to JESD78A}$	II level A

6.3.12 I/O current injection characteristics

As a general rule, current injection to the I/O pins, due to external voltage below V_{SS} or above V_{DDIOx} (for standard, 3.3 V-capable I/O pins) should be avoided during normal product operation. However, in order to give an indication of the robustness of the microcontroller in cases when abnormal injection accidentally happens, susceptibility tests are performed on a sample basis during device characterization.

Functional susceptibility to I/O current injection

While a simple application is executed on the device, the device is stressed by injecting current into the I/O pins programmed in floating input mode. While current is injected into the I/O pin, one at a time, the device is checked for functional failures.

The failure is indicated by an out of range parameter: ADC error above a certain limit (higher than 5 LSB TUE), out of conventional limits of induced leakage current on adjacent pins (out of the -5 μ A/+0 μ A range) or other functional failure (for example reset occurrence or oscillator frequency deviation).

The characterization results are given in Table 46.

Negative induced leakage current is caused by negative injection and positive induced leakage current is caused by positive injection.



OSPEEDRy [1:0] value ⁽¹⁾	Symbol	Parameter	Conditions	Min	Max	Unit
	f _{max(IO)out}	Maximum frequency ⁽³⁾			2	MHz
	t _{f(IO)out}	Output fall time	$C_L = 50 \text{ pF}, V_{DDIOx} \ge 2 \text{ V}$	-	12	20
Fm+	t _{r(IO)out}	Output rise time			34	ns
configuration (4)	f _{max(IO)out}	Maximum frequency ⁽³⁾			0.5	MHz
	t _{f(IO)out}	Output fall time	C _L = 50 pF, V _{DDIOx} < 2 V	-	16	ns
	t _{r(IO)out}	Output rise time			44	115
-	t _{EXTIpw}	Pulse width of external signals detected by the EXTI controller	-	10	-	ns

 Table 49. I/O AC characteristics⁽¹⁾⁽²⁾ (continued)

1. The I/O speed is configured using the OSPEEDRx[1:0] bits. Refer to the STM32F0xxxx RM0091 reference manual for a description of GPIO Port configuration register.

2. Guaranteed by design, not tested in production.

- 3. The maximum frequency is defined in *Figure 20*.
- 4. When Fm+ configuration is set, the I/O speed control is bypassed. Refer to the STM32F0xxxx reference manual RM0091 for a detailed description of Fm+ I/O configuration.

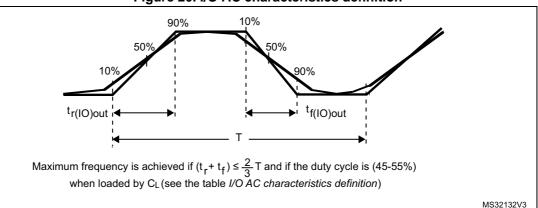


Figure 20. I/O AC characteristics definition

6.3.14 NRST and NPOR pin characteristics

NRST pin characteristics

The NRST pin input driver uses the CMOS technology. It is connected to a permanent pull-up resistor, $\mathsf{R}_{\mathsf{PU}}.$

Unless otherwise specified, the parameters given in the table below are derived from tests performed under the ambient temperature and supply voltage conditions summarized in *Table 20: General operating conditions*.



Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V _{IL(NPOR)}	NPOR Input low level voltage	-	-	-	0.475 V _{DDA} - 0.2 ⁽¹⁾	
V _{IH(NPOR)}	NPOR Input high level voltage	-	0.5 V _{DDA} + 0.2 ⁽¹⁾	-	-	V
V _{hys(NPOR)}	NPOR Schmitt trigger voltage hysteresis	-	-	100 ⁽¹⁾	-	mV
R _{PU}	Weak pull-up equivalent resistor ⁽²⁾	$V_{IN} = V_{SS}$	25	40	55	kΩ

Table 51. NPOR pin characteristics

1. Guaranteed by design, not tested in production.

2. The pull-up is designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance is minimal (\sim 10% order).

6.3.15 12-bit ADC characteristics

Unless otherwise specified, the parameters given in *Table 52* are derived from tests performed under the conditions summarized in *Table 20: General operating conditions*.

Note: It is recommended to perform a calibration after each power-up.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DDA}	Analog supply voltage for ADC ON	-	2.4	-	3.6	V
I _{DDA (ADC)}	Current consumption of the ADC ⁽¹⁾	V _{DDA} = 3.3 V	-	0.9	-	mA
f _{ADC}	ADC clock frequency	-	0.6	-	14	MHz
f _S ⁽²⁾	Sampling rate	12-bit resolution	0.043	-	1	MHz
f _{TRIG} ⁽²⁾	External trigger frequency	f _{ADC} = 14 MHz, 12-bit resolution	-	-	823	kHz
		12-bit resolution	-	-	17	1/f _{ADC}
V _{AIN}	Conversion voltage range	-	0	-	V _{DDA}	V
R _{AIN} ⁽²⁾	External input impedance	See <i>Equation 1</i> and <i>Table 53</i> for details	-	-	50	kΩ
R _{ADC} ⁽²⁾	Sampling switch resistance	-	-	-	1	kΩ
C _{ADC} ⁽²⁾	Internal sample and hold capacitor	-	-	-	8	pF
↓ (2)(3)	Calibration time	f _{ADC} = 14 MHz		5.9		μs
t _{CAL} ⁽²⁾⁽³⁾	Calibration time	-	83			1/f _{ADC}

Table 52. ADC characteristics



T _s (cycles)	t _S (μs)	R _{AIN} max (kΩ) ⁽¹⁾
28.5	2.04	25.2
41.5	2.96	37.2
55.5	3.96	50
71.5	5.11	NA
239.5	17.1	NA

Table 53. R_{AIN} max for f_{ADC} = 14 MHz (continued)

1. Guaranteed by design, not tested in production.

Symbol	Parameter	Test conditions	Тур	Max ⁽⁴⁾	Unit
ET	Total unadjusted error		±1.3	±2	
EO	Offset error	$f_{PCLK} = 48 \text{ MHz},$	±1	±1.5	
EG	Gain error	f _{ADC} = 14 MHz, R _{AIN} < 10 kΩ V _{DDA} = 3 V to 3.6 V	±0.5	±1.5	LSB
ED	Differential linearity error	$T_A = 25 °C$	±0.7	±1	
EL	Integral linearity error		±0.8	±1.5	
ET	Total unadjusted error		±3.3	±4	
EO	Offset error	$f_{PCLK} = 48 \text{ MHz},$	±1.9	±2.8	
EG	Gain error	f _{ADC} = 14 MHz, R _{AIN} < 10 kΩ V _{DDA} = 2.7 V to 3.6 V	±2.8	±3	LSB
ED	Differential linearity error	$T_A = -40$ to 105 °C	±0.7	±1.3	
EL	Integral linearity error		±1.2	±1.7	
ET	Total unadjusted error		±3.3	±4	
EO	Offset error	$f_{PCLK} = 48 \text{ MHz},$	±1.9	±2.8	
EG	Gain error	$f_{ADC} = 14 \text{ MHz}, R_{AIN} < 10 \text{ k}\Omega$ $V_{DDA} = 2.4 \text{ V to } 3.6 \text{ V}$ $T_A = 25 ^{\circ}\text{C}$	±2.8	±3	LSB
ED	Differential linearity error		±0.7	±1.3	
EL	Integral linearity error		±1.2	±1.7	

Table 54. ADC accuracy $^{(1)(2)(3)}$

1. ADC DC accuracy values are measured after internal calibration.

 ADC Accuracy vs. Negative Injection Current: Injecting negative current on any of the standard (non-robust) analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to standard analog pins which may potentially inject negative current. Any positive injection current within the limits specified for I_{INJ(PIN)} and ΣI_{INJ(PIN)} in Section 6.3.13 does not affect the ADC

Any positive injection current within the limits specified for $I_{INJ(PIN)}$ and $\Sigma I_{INJ(PIN)}$ in Section 6.3.13 does not affect the ADC accuracy.

3. Better performance may be achieved in restricted V_{DDA} , frequency and temperature ranges.

4. Data based on characterization results, not tested in production.



Prescaler divider	PR[2:0] bits	Min timeout RL[11:0]= 0x000	Max timeout RL[11:0]= 0xFFF	Unit		
/4	0	0.1	409.6			
/8	1	0.2	819.2			
/16	2	0.4	1638.4			
/32	3	0.8	3276.8	ms		
/64	4	1.6	6553.6			
/128	5	3.2	13107.2			
/256	6 or 7	6.4	26214.4			

Table 58. IWDG min/max timeout period at 40 kHz (LSI)⁽¹⁾

1. These timings are given for a 40 kHz clock but the microcontroller internal RC frequency can vary from 30 to 60 kHz. Moreover, given an exact RC oscillator frequency, the exact timings still depend on the phasing of the APB interface clock versus the LSI clock so that there is always a full RC period of uncertainty.

Prescaler	WDGTB	Min timeout value	Max timeout value	Unit
1	0	0.0853	5.4613	
2	1	0.1706	10.9226	me
4	2	0.3413	21.8453	ms
8	3	0.6826	43.6906	

Table 59. WWDG min/max timeout value at 48 MHz (PCLK)

6.3.19 Communication interfaces

I²C interface characteristics

The I^2C interface meets the timings requirements of the I^2C -bus specification and user manual rev. 03 for:

- Standard-mode (Sm): with a bit rate up to 100 kbit/s
- Fast-mode (Fm): with a bit rate up to 400 kbit/s
- Fast-mode Plus (Fm+): with a bit rate up to 1 Mbit/s.

The I²C timings requirements are guaranteed by design when the I2Cx peripheral is properly configured (refer to Reference manual).

The SDA and SCL I/O requirements are met with the following restrictions: the SDA and SCL I/O pins are not "true" open-drain. When configured as open-drain, the PMOS connected between the I/O pin and V_{DDIOx} is disabled, but is still present. Only FTf I/O pins support Fm+ low level output current maximum requirement. Refer to Section 6.3.13: I/O port characteristics for the I²C I/Os characteristics.

All I²C SDA and SCL I/Os embed an analog filter. Refer to the table below for the analog filter characteristics:



Symbol	Max	Unit		
t _{AF}	Maximum width of spikes that are suppressed by the analog filter	50 ⁽²⁾	260 ⁽³⁾	ns

Table 60. I²C analog filter characteristics⁽¹⁾

1. Guaranteed by design, not tested in production.

2. Spikes with widths below $t_{AF(min)}$ are filtered.

3. Spikes with widths above $t_{AF(max)}$ are not filtered

SPI/I²S characteristics

Unless otherwise specified, the parameters given in *Table 61* for SPI or in *Table 62* for I^2S are derived from tests performed under the ambient temperature, f_{PCLKx} frequency and supply voltage conditions summarized in *Table 20: General operating conditions*.

Refer to Section 6.3.13: I/O port characteristics for more details on the input/output alternate function characteristics (NSS, SCK, MOSI, MISO for SPI and WS, CK, SD for I²S).

Symbol	Parameter	Conditions	Min	Max	Unit	
f _{SCK} 1/t _{c(SCK)}	SPI clock frequency	Master mode	-	18	MHz	
		Slave mode	-	18	IVIHZ	
t _{r(SCK)} t _{f(SCK)}	SPI clock rise and fall time	Capacitive load: C = 15 pF	-	6	ns	
t _{su(NSS)}	NSS setup time	Slave mode	4Tpclk	-		
t _{h(NSS)}	NSS hold time	Slave mode	2Tpclk + 10	-	ns	
t _{w(SCKH)} t _{w(SCKL)}	SCK high and low time	Master mode, f _{PCLK} = 36 MHz, presc = 4	Tpclk/2 -2	Tpclk/2 + 1		
t _{su(MI)}	Data input setup time	Master mode	4	-		
t _{su(SI)}		Slave mode	5	-		
t _{h(MI)}	Data input hold time	Master mode	4	-		
t _{h(SI)}	Data input hold time	Slave mode	5	-		
t _{a(SO)} ⁽²⁾	Data output access time	Slave mode, f _{PCLK} = 20 MHz	0	3Tpclk		
t _{dis(SO)} ⁽³⁾	Data output disable time	Slave mode	0	18		
t _{v(SO)}	Data output valid time	Slave mode (after enable edge)	-	22.5	1	
t _{v(MO)}	Data output valid time	Master mode (after enable edge)	-	6		
t _{h(SO)}	Data output hold time	Slave mode (after enable edge)	11.5	-		
t _{h(MO)}	Data output hold time	Master mode (after enable edge)	2	-		
DuCy(SCK)	SPI slave input clock duty cycle	Slave mode	25	75	%	

Table	61.	SPI	characteristics ⁽¹	I)
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1. Data based on characterization results, not tested in production.

2. Min time is for the minimum time to drive the output and the max time is for the maximum time to validate the data.

3. Min time is for the minimum time to invalidate the output and the max time is for the maximum time to put the data in Hi-Z



7 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK[®] is an ST trademark.

7.1 UFQFPN48 package information

UFQFPN48 is a 48-lead, 7x7 mm, 0.5 mm pitch, ultra-thin fine-pitch quad flat package.

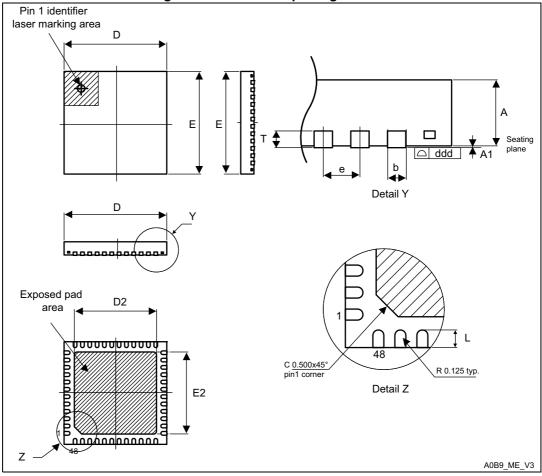


Figure 29. UFQFPN48 package outline

1. Drawing is not to scale.

- 2. All leads/pads should also be soldered to the PCB to improve the lead/pad solder joint life.
- 3. There is an exposed die pad on the underside of the UFQFPN package. It is recommended to connect and solder this back-side pad to PCB ground.

